

SiC MOS Interface Mini Workshop at University of Tokyo

Taking opportunity of the visit of Prof. Leonard Feldman, we are going to have a mini workshop on SiC MOS interface at the University of Tokyo. Those who are interested in material science of semiconductor interfaces, especially SiC/SiO₂ interface, are welcomed to join the workshop.

Date: **Nov. 15, 2019 (14:00 – 17:00)**

Place: **Seminar Room #205, in Engineering Building 4 (1F)**

Hongo Campus, The University of Tokyo

7-3-1 Hongo, Bunkyo-ku, Tokyo 113-8656

< Workshop Resume >

Chair: Koji Kita, Department of Materials Engineering, The University of Tokyo

14:00 Special lecture

Lecturer: Prof. Leonard Feldman,
Rutgers University

Institute for Advanced Materials, Devices and Nanotechnology

Title: *“Materials Science of the SiC(4H)/SiO₂ Interface”*



(15:00~ Coffee break)

15:30 Discussions : Recent topics on SiC surface and interface

- Prof. Yuichiro Matsushita (Tokyo Institute of Technology)
“Ab-initio study on surface and interface structures of 4H-SiC”
- Dr. Hirohisa Hirai (AIST)
“Elimination of traps and scattering centers by NO Annealing from 4H-SiC Interfaces”
- Tae-Hyon Kil and Prof. Koji Kita (The University of Tokyo)
“Anomalous band alignment change of SiO₂/4H-SiC Interfaces induced by NO-POA”

17:00 Free discussions & closing

17:30~ Leave for Dinner at Nikutei FUTAGO (in 10-15 min. walk)